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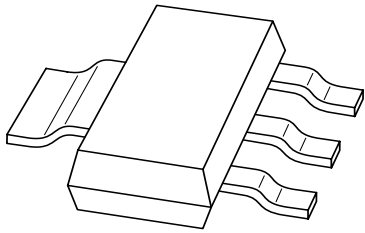
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Kind regards,

Team Nexperia

DATA SHEET



PZTA44 NPN high-voltage transistor

Product data sheet
Supersedes data of 1998 Nov 26

1999 May 21

NPN high-voltage transistor

PZTA44

FEATURES

- Low current (max. 300 mA)
- High voltage (max. 400 V).

APPLICATIONS

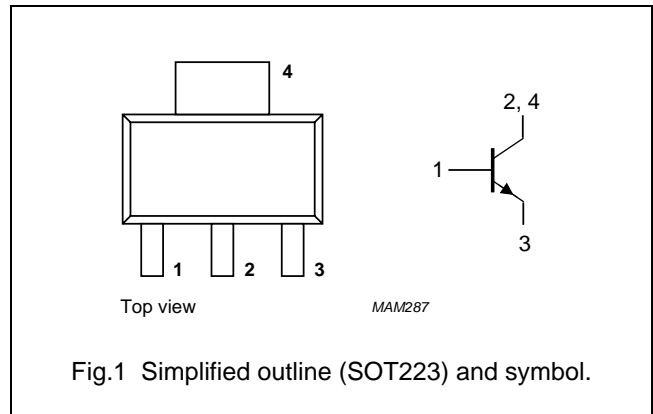
- Telecommunication.

DESCRIPTION

NPN high-voltage transistor in a SOT223 plastic package.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	500	V
V_{CEO}	collector-emitter voltage	open base	–	400	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	300	mA
I_{CM}	peak collector current		–	300	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	1.35	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

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PZTA44

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	91	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		10	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 400\text{ V}$	–	100	nA
		$I_E = 0; V_{CB} = 400\text{ V}; T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$	40	–	
		$I_C = 10\text{ mA}$	50	200	
		$I_C = 50\text{ mA}; \text{note 1}$	45	–	
		$I_C = 100\text{ mA}; \text{note 1}$	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1\text{ mA}; I_B = 0.1\text{ mA}$	–	400	mV
		$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	500	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	750	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}; \text{note 1}$	–	850	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 20\text{ V}; f = 1\text{ MHz}$	–	7	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	180	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	20	–	MHz

Note

1. Pulse test: $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02$.

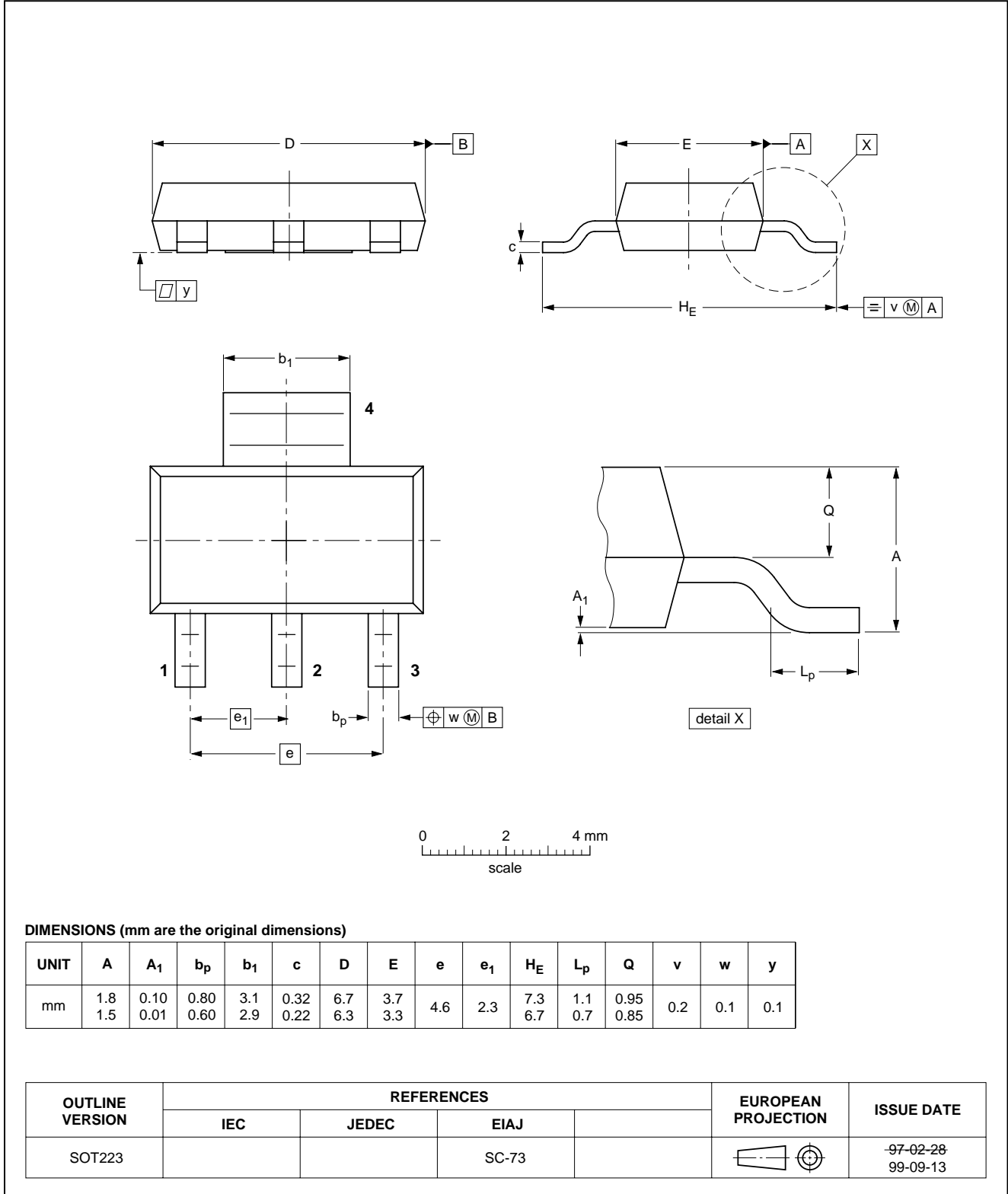
NPN high-voltage transistor

PZTA44

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN high-voltage transistor

PZTA44

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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